

THYRISTOR MODULE

PFT2014N

200A / 400V

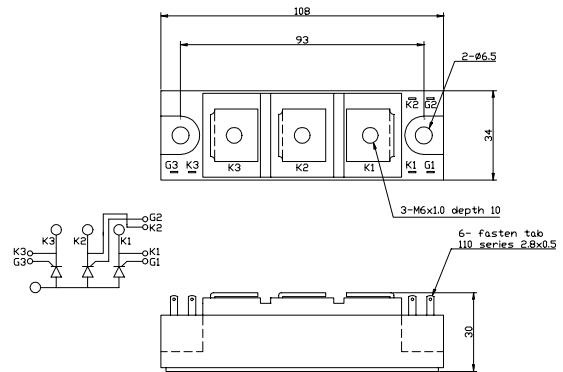
FEATURES

- * 3 Phase Anode Common
Half Bridge Circuit
- * High Surge Capability
- * UL Recognized, File No. E187184

TYPICAL APPLICATIONS

- * Rectified For General Use

OUTLINE DRAWING



Maximum Ratings

Approx Net Weight:300g

Parameter	Symbol	Grade	Unit
		PFT2014N	
Repetitive Peak Off-State Voltage	V_{DRM}	400	V
Non Repetitive Peak Off-State Voltage	V_{DSM}	500	
Repetitive Peak Reverse Voltage	V_{RRM}	400	V
Non Repetitive Peak Reverse Voltage	V_{RSM}	500	

Parameter		Conditions	Max Rated Value	Unit		
Average Rectified Output Current	$I_{O(AV)}$	50Hz Half Sine Wave condition $T_c=116^{\circ}C$	200	A		
RMS On-State Current	$I_{T(RMS)}$		314	A		
Surge On-State Current	I_{TSM}	50 Hz Half Sine Wave, 1Pulse, Non-Repetitive	5000	A		
I Squared t	I^2t	2msec to 10msec	125000	A^2s		
Peak Gate Power	P_{GM}		5	W		
Average Gate Power	$P_{G(AV)}$		1	W		
Peak Gate Current	I_{GM}		2	A		
Peak Gate Voltage	V_{GM}		10	V		
Peak Gate Reverse Voltage	V_{RGM}		5	V		
Operating JunctionTemperature Range	T_{jw}		-40 to +150	$^{\circ}C$		
Storage Temperature Range	T_{stg}		-40 to +125	$^{\circ}C$		
Mounting torque	Case mounting	Ftor	Greased	M6 Screw	2.5 to 3.5	N.m
	Terminals		M6 Screw			

Value per 1 Arm

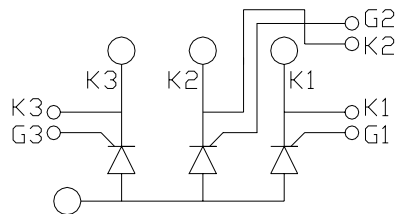
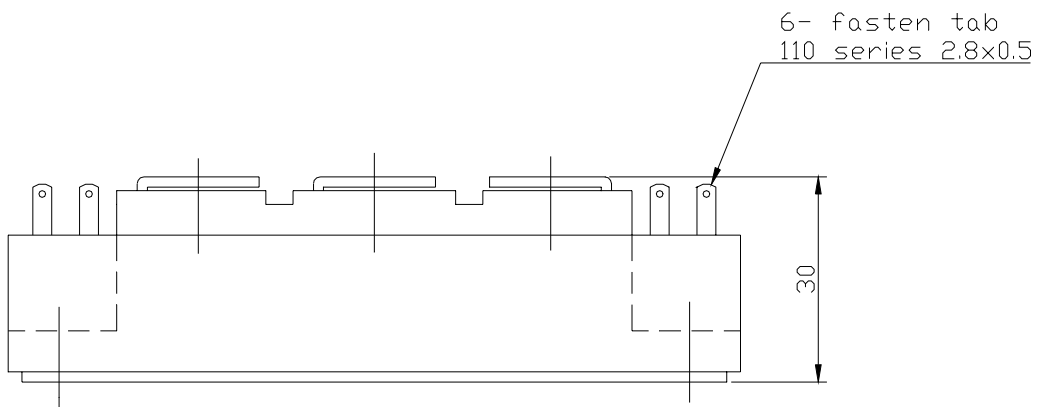
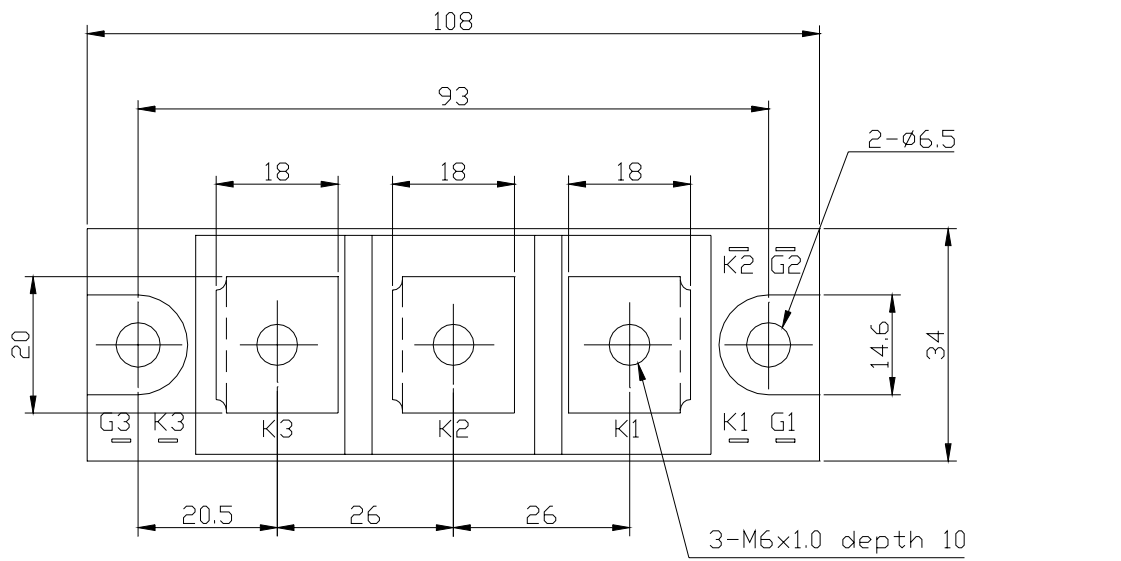
Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Maximum Value.			Unit
			Min.	Typ.	Max.	
Peak Off-State Current	I_{DM}	$V_{DM} = V_{DRM}, T_j = 150^\circ\text{C}$			50	mA
Peak Reverse Current	I_{RM}	$V_{RM} = V_{RRM}, T_j = 150^\circ\text{C}$			50	mA
Peak Forward Voltage	V_{TM}	$I_{TM} = 600\text{A}, T_j = 25^\circ\text{C}$			1.19	V
Gate Current to Trigger	I_{GT}	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		300	mA
			$T_j = 25^\circ\text{C}$		150	
			$T_j = 125^\circ\text{C}$		60	
Gate Voltage to Trigger	V_{GT}	$V_D = 6\text{V}, I_T = 1\text{A}$	$T_j = -40^\circ\text{C}$		5.0	V
			$T_j = 25^\circ\text{C}$		3.0	
			$T_j = 125^\circ\text{C}$		1.5	
Gate Non-Trigger Voltage	V_{GD}	$V_D = 2/3V_{DRM}, T_j = 125^\circ\text{C}$	0.25			V
Latching Current	I_L	$T_j = 25^\circ\text{C}$		150		mA
Holding Current	I_H	$T_j = 25^\circ\text{C}$		100		mA
Thermal Resistance *1	$R_{th(j-c)}$	Junction to Case			0.05	$^\circ\text{C/W}$

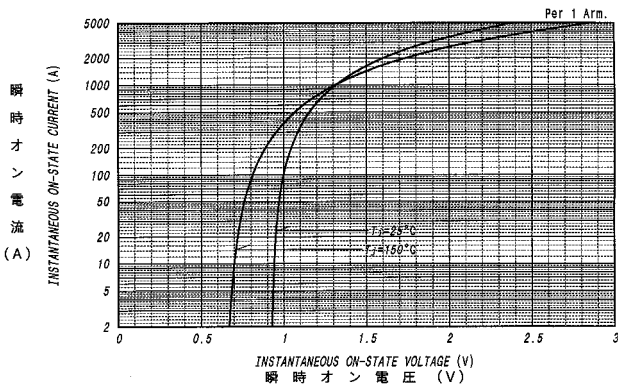
Value Per 1Arm

*1:Value Per Module

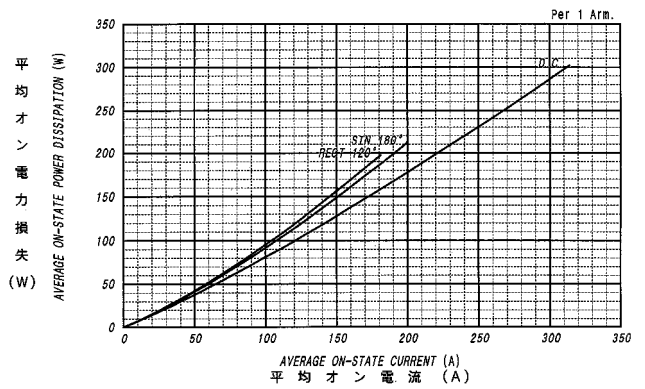
PFT2014N OUTLINE DRAWING (Dimensions in mm)



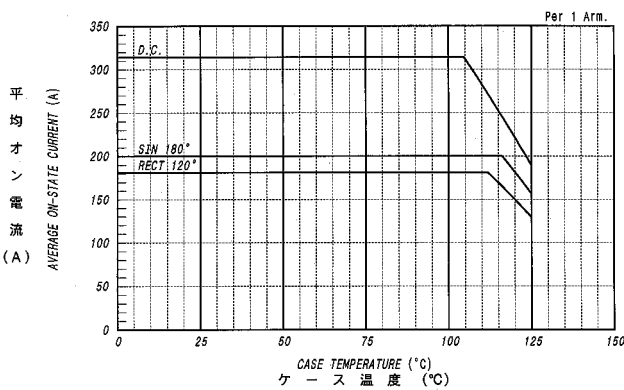
オン電圧特性
ON-STATE CURRENT VS. VOLTAGE



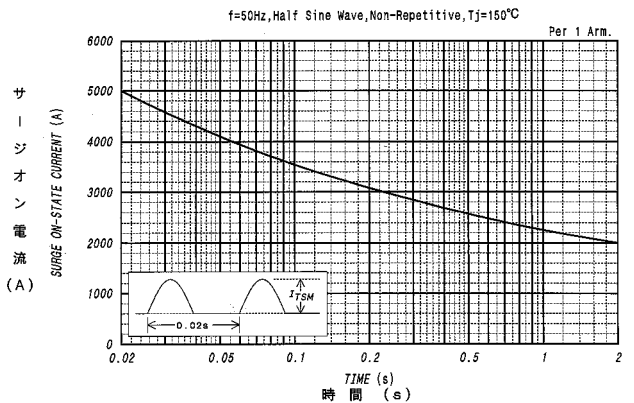
平均オン電力損失特性
AVERAGE ON-STATE POWER DISSIPATION



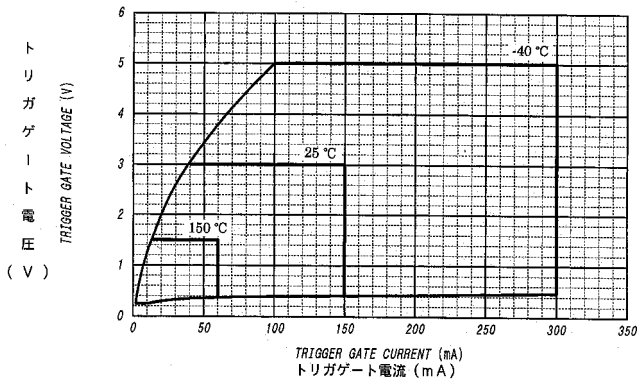
平均オン電流 - ケース温度定格
AVERAGE ON-STATE CURRENT VS. CASE TEMPERATURE



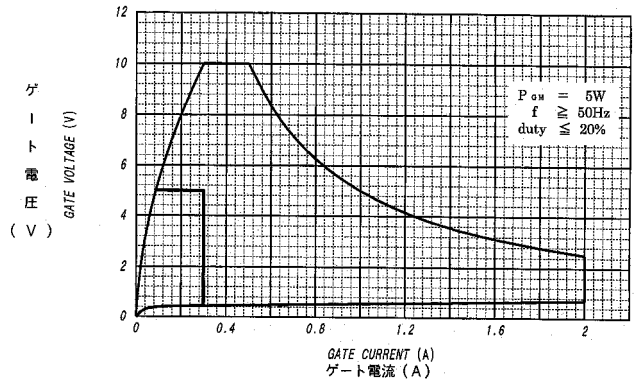
サージオン電流定格
SURGE CURRENT RATINGS



ゲート特性
GATE CHARACTERISTICS



ゲート定格
GATE RATINGS



過渡熱抵抗特性
MAXIMUM TRANSIENT THERMAL IMPEDANCE
Junction to Case

